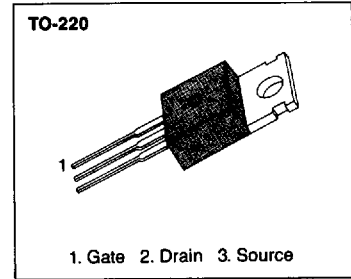


FEATURES

- Lower $R_{DS(on)}$
- Improved inductive ruggedness
- Fast switching times
- Rugged polysilicon gate cell structure
- Lower input capacitance
- Extended safe operating area
- Improved high temperature reliability



PRODUCT SUMMARY

Part Number	V _{DS}	R _{DS(on)}	I _D
IRF9610	-200V	3.0Ω	-1.75A
IRF9611	-150V	3.0Ω	-1.75A

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	IRF9610	IRF9611	Unit
Drain-Source Voltage (1)	V _{DSS}	-200	-150	V _{dc}
Drain-Gate Voltage (R _{GS} =1.0MΩ)(1)	V _{BGR}	-200	-150	V _{dc}
Gate-Source Voltage	V _{GS}	±20		V _{dc}
Continuous Drain Current T _C =25 °C	I _D	-1.75		A _{dc}
Continuous Drain Current T _C =100 °C	I _D	-1.0		A _{dc}
Drain Current - Pulsed (3)	I _{DM}	-7.0		A _{dc}
Gate Current - Pulsed	I _{GM}	±1.5		A _{dc}
Single Pulsed Avalanche Energy (4)	E _{AS}	110		mJ
Avalanche Current	I _{AS}	-1.75		A
Total Power Dissipation @ T _C =25 °C	P _D	20		Watts
Derate above 25 °C		0.16		W/°C
Operating and Storage	T _J , T _{STG}	-55 to +150		°C
Junction Temperature Range				
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T _L	300		°C

Notes : (1) T_J=25°C to 150°C

(2) Pulse test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%

(3) Repetitive rating : Pulse width limited by max. junction temperature

(4) L=59mH, V_{dd}=-50V, R_G=25Ω, Starting T_J=25°C

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-Source Breakdown Voltage					
	IRF9610	-200	-	-	V	V _{GS} =0V, I _D =-250 μ A
	IRF9611	-150	-	-	V	
V _{GS(th)}	Gate Threshold Voltage	-2.0	-	-4.0	V	V _{DS} =V _{GS} , I _D =-250 μ A
I _{GSS}	Gate-Source Leakage Forward	-	-	-100	nA	V _{GS} =-20V
I _{GSS}	Gate-Source Leakage Reverse	-	-	100	nA	V _{GS} =20V
I _{DSS}	Zero Gate Voltage Drain Current	-	-	-250	μ A	V _{DS} =-Max. Rating, V _{GS} =0V
		-	-	-1000	μ A	V _{DS} =-0.8 Max. Rating, V _{GS} =0V, T _C =125 $^\circ$ C
R _{DS(on)}	Static Drain-Source On Resistance(2)	-	-	3.0	Ω	V _{GS} =-10V, I _D =-0.9A
g _{fs}	Forward Transconductance (2)	0.7	-	-	U	V _{DS} \leq -50V, I _D =-0.9A
C _{iss}	Input Capacitance	-	227	-	pF	V _{GS} =0V, V _{DS} =-25V, f=1.0MHz
C _{oss}	Output Capacitance	-	52.7	-	pF	
C _{rss}	Reverse Transfer Capacitance	-	29.6	-	pF	
t _{d(on)}	Turn-On Delay Time	-	-	15	ns	V _{DD} =-0.5BV _{DSS} , I _D =-1.75A, Z _O =24 Ω
t _r	Rise Time	-	-	25	ns	(MOSFET switching times are essentially independent of operating temperature)
t _{d(off)}	Turn-Off Delay Time	-	-	15	ns	
t _f	Fall Time	-	-	15	ns	
Q _g	Total Gate Charge (Gate-Source Plus Gate-Drain)	-	-	18	nC	V _{GS} =-10V, I _D =-1.75A, V _{DS} =-0.8 Max. Rating (Gate charge is essentially independent of operating temperature)
Q _{gs}	Gate-Source Charge	-	2.6	-	nC	
Q _{gd}	Gate-Drain ("Miller") Charge	-	7.6	-	nC	

THERMAL RESISTANCE

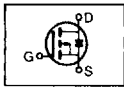
Symbol	Characteristics		All	Units	Remark
R _{thJC}	Junction-to-Case	MAX	3.5	K/W	
R _{thCS}	Case-to-Sink	TYP	0.5	K/W	Mounting surface flat smooth, and greased
R _{thJA}	Junction-to-Ambient	MAX	62.5	K/W	Free Air Operation

Notes : (1) T_J=25 $^\circ$ C to 150 $^\circ$ C

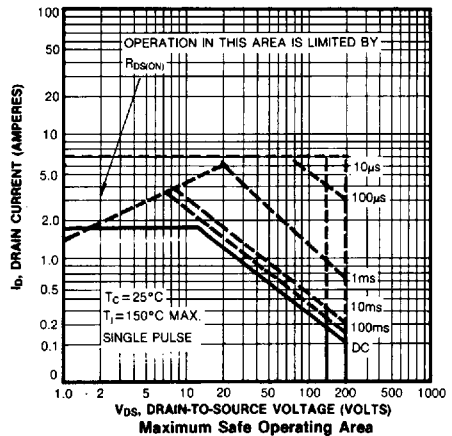
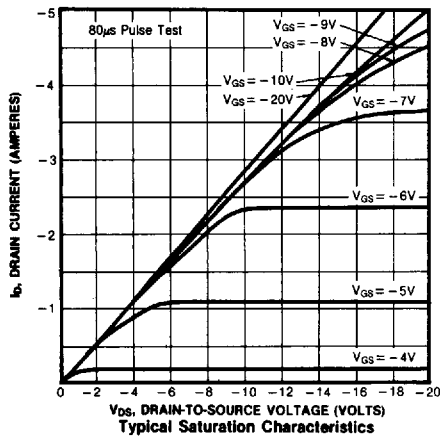
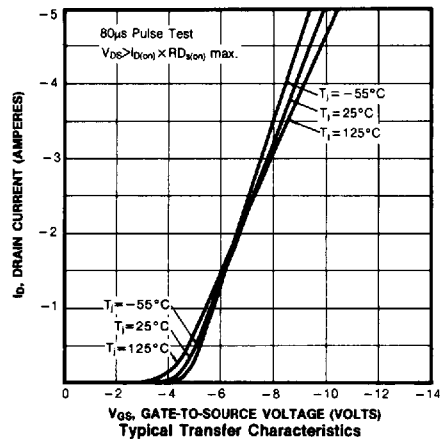
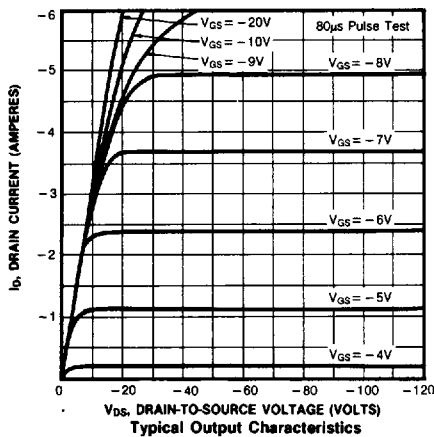
(2) Pulse test : Pulse width \leq 300 μ s, Duty Cycle \leq 2%

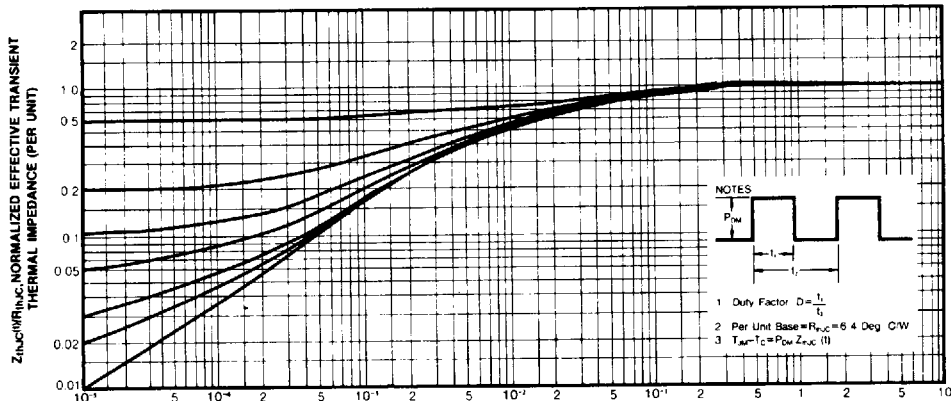
(3) Repetitive rating : Pulse width limited by max. junction temperature

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

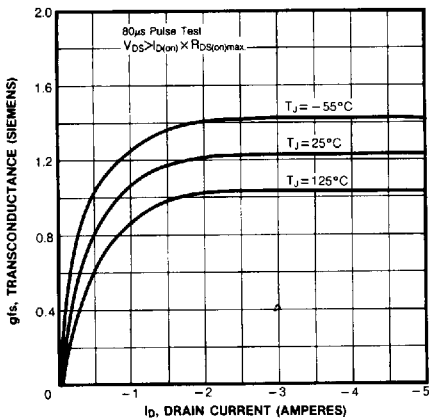
Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	-	-	-1.75	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier 
I _{SM}	Pulse Source Current (Body Diode) (3)	-	-	-7.0	A	
V _{SD}	Diode Forward Voltage (2)	-	-	-5.8	V	T _J =25°C, I _S =-1.75A, V _{GS} =0V
t _r	Reverse Recovery Time	-	240	-	ns	T _J =25°C, I _F =-1.75A, dI _F /dt=100A/μS

- Notes : (1) T_J=25°C to 150°C
 (2) Pulse test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%
 (3) Repetitive rating : Pulse width limited by max. junction temperature

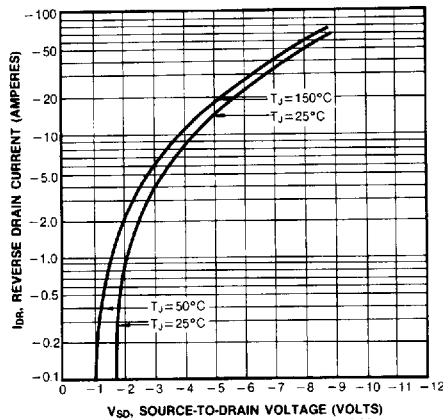




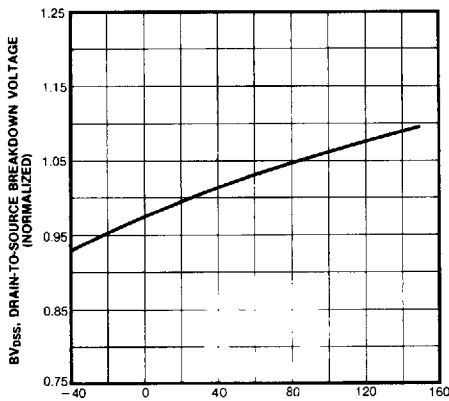
11. SQUARE WAVE PULSE DURATION (SECONDS)
Maximum Effective Transient Thermal Impedance Junction-to-Case Vs. Pulse Duration



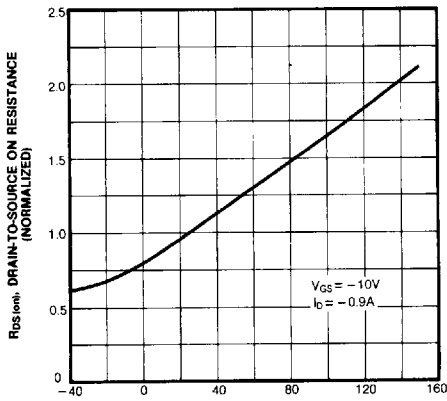
Typical Transconductance Vs. Drain Current



Typical Source-Drain Diode Forward Voltage



Breakdown Voltage Vs. Temperature



Normalized On-Resistance Vs. Temperature

4

